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L Number	Hits	Search Text	DB	Time stamp
29	27002	((chemical near5 mechanical near5	USPAT;	2003/05/28 19:05
		polish\$3) CMP)	US-PGPUB	
30	12626	(((chemical near5 mechanical near5	USPAT;	2003/05/28 19:06
		polish\$3) CMP)) and ((insulat\$3 dielectric	US-PGPUB	
		oxide) and planar\$6 and (conduct\$6		
2.1	0056	polysilicon))	TIODAM.	2002/05/20 10:06
31	8056	((((chemical near5 mechanical near5	USPAT; US-PGPUB	2003/05/28 19:06
		polish\$3) CMP)) and ((insulat\$3 dielectric oxide) and planar\$6 and (conduct\$6	US-PGPUB	
		polysilicon))) and selectiv\$6		
36	4447	(((((chemical near5 mechanical near5	USPAT;	2003/05/28 18:36
		polish\$3) CMP)) and ((insulat\$3 dielectric	US-PGPUB	2000, 00, 20 20100
		oxide) and planar\$6 and (conduct\$6		
		polysilicon))) and selectiv\$6) and rate		
37	3681	(((((chemical near5 mechanical near5	USPAT;	2003/05/28 18:37
		polish\$3) CMP)) and ((insulat\$3 dielectric	US-PGPUB	
		oxide) and planar\$6 and (conduct\$6		ļ
		polysilicon))) and selectiv\$6) and rate)		
		and (first near5 (layer material film))		
38	3488	((((((chemical near5 mechanical near5	USPAT;	2003/05/28 18:38
		polish\$3) CMP)) and ((insulat\$3 dielectric	US-PGPUB	
		oxide) and planar\$6 and (conduct\$6		
		polysilicon))) and selectiv\$6) and rate) and (second near5 (layer material film))		
39	1588	((((((chemical near5 mechanical near5	USPAT;	2003/05/28 18:39
	1300	polish\$3) CMP)) and ((insulat\$3 dielectric	US-PGPUB	2003/03/20 18.39
		oxide) and planar\$6 and (conduct\$6	00 10100	
		polysilicon))) and selectiv\$6) and rate)		į
		and (third near5 (layer material film))		
40	3298	((((((chemical near5 mechanical near5	USPAT;	2003/05/28 18:40
		polish\$3) CMP)) and ((insulat\$3 dielectric	US-PGPUB	}
		oxide) and planar\$6 and (conduct\$6		
		polysilicon))) and selectiv\$6) and rate)		
		and (first near5 (layer material film)))		
		and (((((((chemical near5 mechanical near5		-
		polish\$3) CMP)) and ((insulat\$3 dielectric		
		oxide) and planar\$6 and (conduct\$6 polysilicon))) and selectiv\$6) and rate)		ļ
		and (second near5 (layer material film)))		
41	1526	((((((chemical near5 mechanical near5	USPAT;	2003/05/28 18:41
	1320	polish\$3) CMP)) and ((insulat\$3 dielectric	US-PGPUB	2003/03/20 10.41
	}	oxide) and planar\$6 and (conduct\$6		
	,	polysilicon))) and selectiv\$6) and rate)		
		and (first near5 (layer material film)))		
	}	and ((((((chemical near5 mechanical near5		
		polish\$3) CMP)) and ((insulat\$3 dielectric		
		oxide) and planar\$6 and (conduct\$6		
		polysilicon))) and selectiv\$6) and rate)		
		and (second near5 (layer material film)))	ļ	
	<u>.</u>	and (((((((chemical near5 mechanical near5		
 		polish\$3) CMP)) and ((insulat\$3 dielectric oxide) and planar\$6 and (conduct\$6		
		polysilicon))) and selectiv\$6) and rate)		
l		and (third near5 (layer material film)))		
42	9426	((chemical near5 mechanical near5	EPO; JPO;	2003/05/28 19:06
		polish\$3) CMP)	DERWENT;	=====================================
			IBM TDB	
43	409	(((chemical near5 mechanical near5	EPO; JPO;	2003/05/28 19:06
		polish\$3) CMP)) and ((insulat\$3 dielectric	DERWENT;	
		oxide) and planar\$6 and (conduct\$6	IBM_TDB	
	{	polysilicon))		